

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	I_D
1500V	5Ω@10V	3A

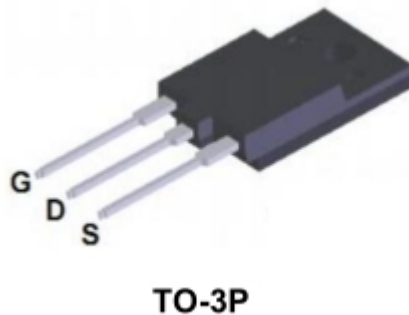
Feature

- Fast Switching
- Low Gate Charge and Rdson
- 100% Single Pulse avalanche energy Test
- Low Reverse transfer capacitances

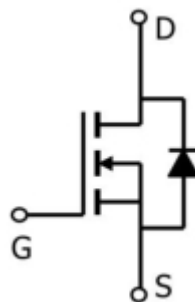
Application

- Power switch circuit of adaptor and charger

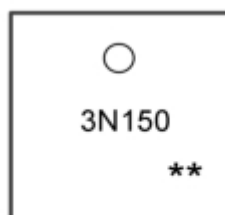
Package



Circuit diagram



Marking



3N150

=Device Code
=Week Code

Absolute maximum ratings

(T_a=25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V _{DS}	1500	V
Gate-Source Voltage	V _{GS}	±30	V
Continuous Drain Current ¹ (T _C =25°C)	I _D	3	A
Pulsed Drain Current ²	I _{DM}	12	A
Single Pulse Avalanche Energy ³	E _{AS}	184	mJ
Peak Diode Recovery dv/dt	dv/dt	5	V/ns
Total Power Dissipation(T _C =25°C)	P _D	32	W
Thermal Resistance Junction-Case ¹	R _{θJC}	3.9	°C/ W
Storage Temperature Range	T _{STG}	-55~ +150	°C
Operating Junction Temperature Range	T _J	-55~ +150	°C

Electrical characteristics

($T_A=25^{\circ}\text{C}$, unless otherwise noted)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Static Characteristics						
Drain-source breakdown voltage	BV_{DSS}	$V_{GS} = 0V, I_D = 250\mu A$	1500			V
Bvdss Temperature Coefficient	$\Delta BV_{DSS}/\Delta T$	$I_D = 250\mu A, \text{Reference } 25^{\circ}C$		1.5		V/ $^{\circ}C$
Drain-Source Leakage Current	I_{DSS}	$V_{DS} = 1500V, V_{GS} = 0V$ $T_J = 25^{\circ}C$			25	μA
Gate-Source Leakage Current	I_{GSS}	$V_{GS} = \pm 30V, V_{DS} = 0V$			± 100	μA
Gate threshold voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	3	4	5	V
Static Drain-Source on-Resistance	$R_{DS(on)}$	$V_{GS} = 10V, I_D = 1A$		5	6.5	Ω
Dynamic characteristics						
Input Capacitance	C_{iss}	$V_{DS} = 25V, V_{GS} = 0V,$ $f = 1MHz$		2036		pF
Output Capacitance	C_{oss}			98		
Reverse Transfer Capacitance	C_{rss}			2.8		
Switching Characteristics						
Total Gate Charge	Q_g	$V_{DS} = 750V, V_{GS} = 10V,$ $I_D = 3A$		37.6		nC
Gate-Source Charge	Q_{gs}			9.9		
Gate-Drain Charge	Q_{gd}			14.4		
Turn-On Delay Time	$T_{d(on)}$	$V_{DD} = 750V, V_{GS} = 10V,$ $R_G = 10\Omega, I_D = 3A$		35.8		nS
Rise Time	T_r			19.4		
Turn-Off Delay Time	$T_{d(off)}$			56		
Fall Time	T_f			31.2		
Source-Drain Diode Characteristics						
Diode Forward Voltage	V_{SD}	$I_S = 1.8A, V_{GS} = 0V$			1.5	V
Reverse Recovery Time	t_{rr}	$I_S = 4.8A, T_J = 25^{\circ}C$ $di_F/dt = 100A/\mu s, V_{GS} = 0V$		105		ns
Reverse Recovery Charge	Q_{rr}			380		nC
Reverse Recovery Current	I_{RRM}			7.2		A

Notes:

- 1.The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
- 2.The data tested by pulsed , pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$
- 3.The EAS data shows Max. rating . The test condition is $I_D = 5A, L = 10mH$

Typical Characteristics

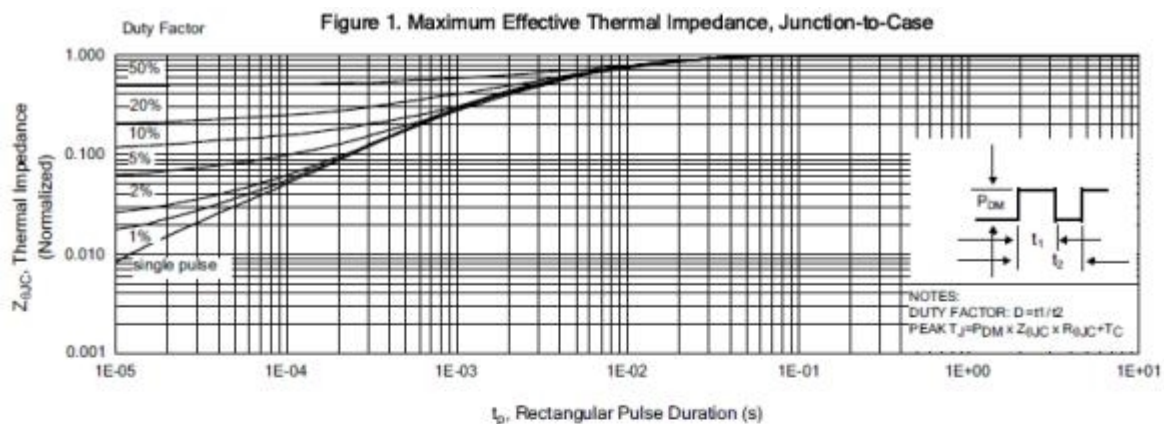


Figure 2. Maximum Power Dissipation vs Case Temperature

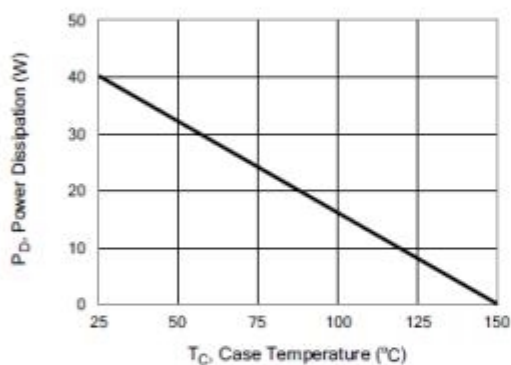


Figure3. Maximum Continuous Drain Current vs Case Temperature

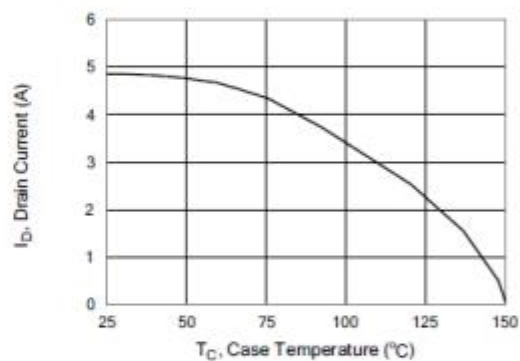


Figure 4. Typical Output Characteristics

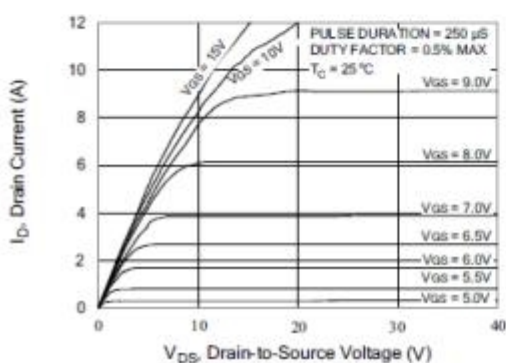


Figure5. Typical Drain-to-Source ON Resistance vs Gate Voltage and Drain Current

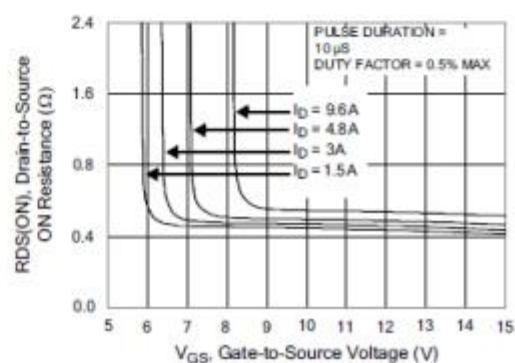


Figure 6. Maximum Peak Current Capability

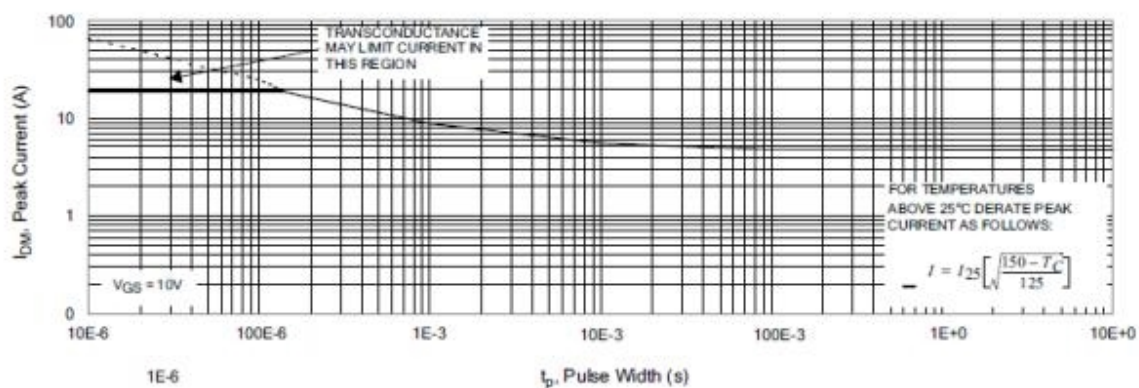


Figure 7. Typical Transfer Characteristics

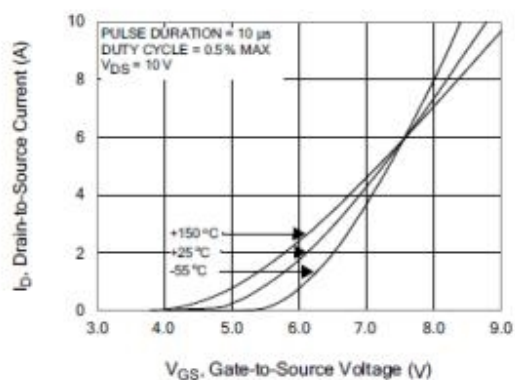


Figure 8. Unclamped Inductive Switching Capability

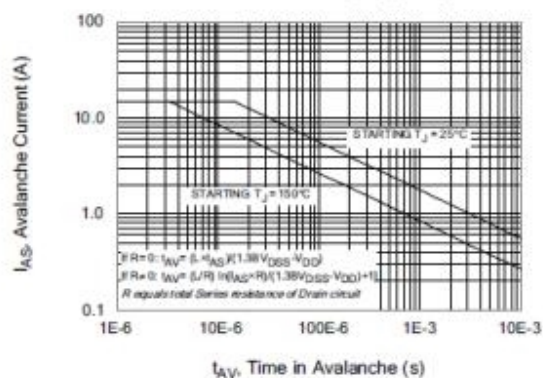


Figure 9. Typical Drain-to-Source ON Resistance vs Drain Current

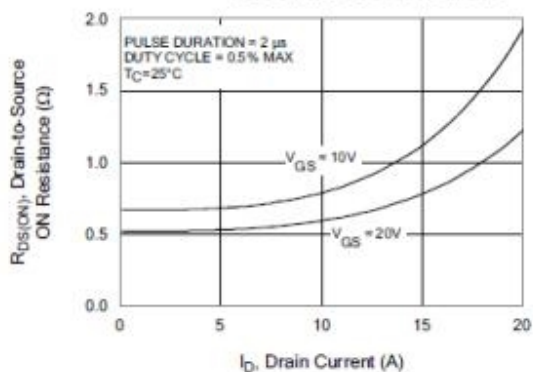


Figure 10. Typical Drain-to-Source ON Resistance vs Junction Temperature

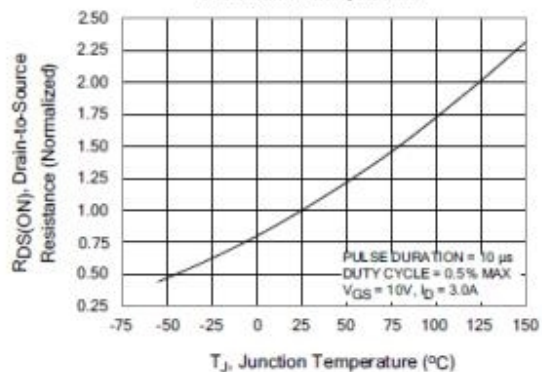


Figure 11. Typical Breakdown Voltage vs Junction Temperature

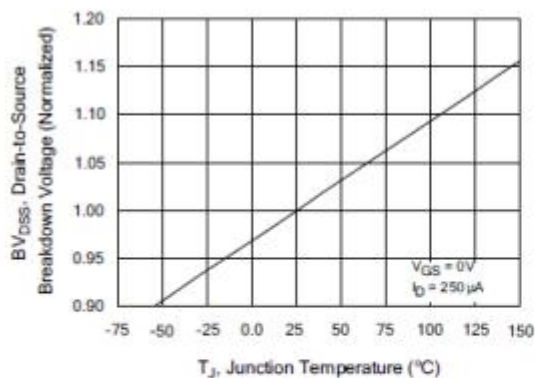


Figure 12. Typical Threshold Voltage vs Junction Temperature

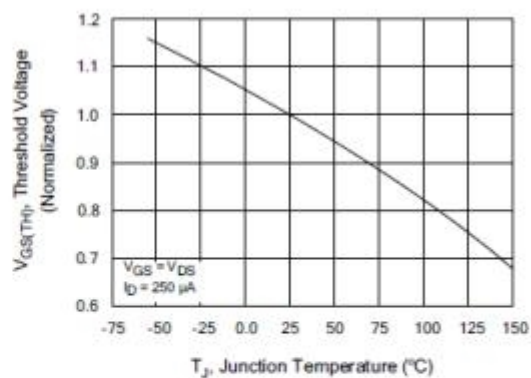


Figure 13. Maximum Forward Bias Safe Operating Area

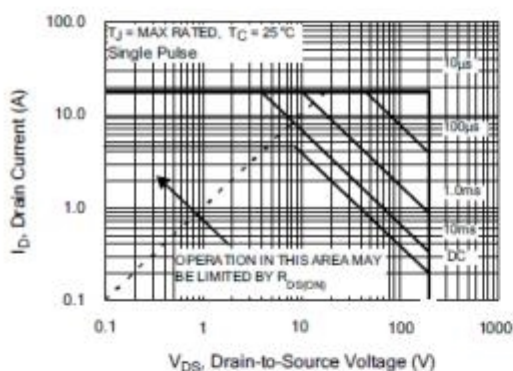


Figure 14. Typical Capacitance vs Drain-to-Source Voltage

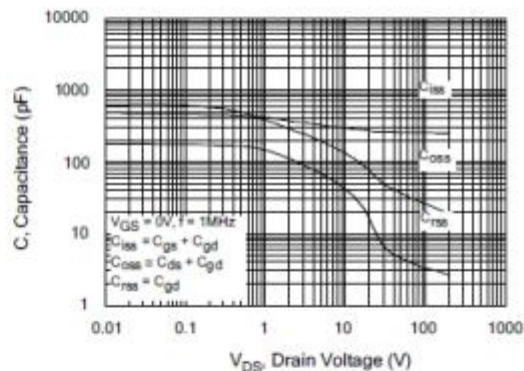


Figure 15. Typical Gate Charge vs Gate-to-Source Voltage

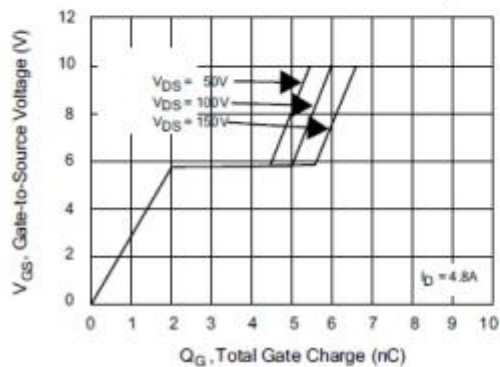
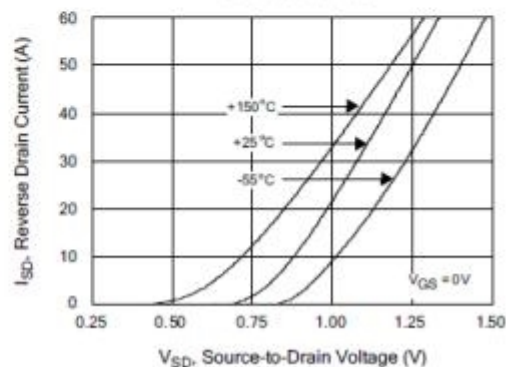
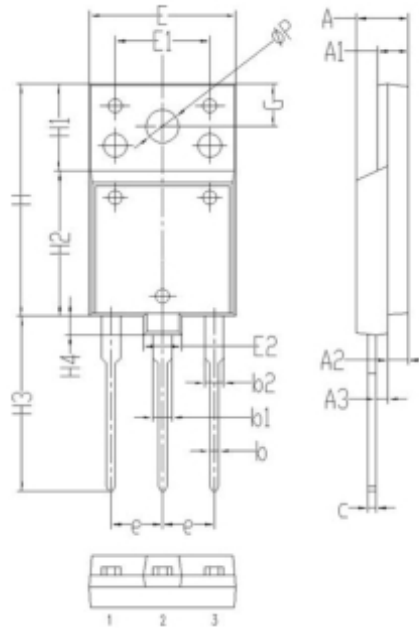


Figure 16. Typical Body Diode Transfer Characteristics



TO-3P Package Information



Items	Values(mm)	
	MIN	MAX
A	5.25	5.85
A1	2.7	3.3
A2	1.8	2.4
A3	1.0	1.6
b	0.45	1.05
b1	1.7	2.3
b2	1.7	2.3
c	0.6	1.2
e	5.15	5.75
E	15.2	15.8
E1	9.7	10.3
E2	3.7	4.3
H	24.2	24.8
H1	8.9	9.5
H2	15.0	15.6
H3	17.9	19.1
H4	1.7	2.3
H5	4.7	5.3
G	4.2	4.8
ΦP	3.3	3.9